

Ab initio study of the double row model of the Si(553)-Au reconstruction

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Abstract

Using x-ray diffraction Ghose et al. [Surf. Sci. 581 (2005) 199] have recently produced a structural model for the quantum-wire surface Si(553)-Au. This model presents two parallel gold wires located at the step edge. Thus, the structure and the gold coverage are quite different from previous proposals. We present here an ab initio study using density functional theory of the stability, electronic band structure and scanning tunneling microscopy images of this model.

1 Introduction

One of the most interesting properties of the one-dimensional metals is the breakdown of the Fermi-liquid behavior. The nature of the low-energy excitations is in this case quite different from the expectations based on the Fermi liquid theory. The single-particle excitations have to be replaced by separate spin and charge collective excitations [1]. This collective behavior leads to several exotic phases at low temperatures. However, although these theoretical predictions are clear and well-founded, the observation of the spin-charge

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separation and other effects has proven quite elusive. One of the main problems to observe this metallic and non-Fermi-liquid ground state (the so-called Luttinger liquid) is the instability of the one-dimensional metals against the Peierls distortion [2] and, in some cases, the Mott insulating state [3].

Atomic-thin gold wires are spontaneously formed on several vicinal Si(111) surfaces after the deposition of gold in the sub-monolayer regime. Each terrace contains at least one of these gold wires running parallel to the step-edge. These surface reconstructions have been proposed as excellent model systems to probe the electronic properties of one-dimensional metals and, consequently, have attracted much attention in recent years [4]. Some examples that have been extensively studied are the Si(557)-Au [5,13] and the Si(111)-(5 \times 2)-Au [14,24] reconstructions. These surfaces have been suggested to present several advantages over other quasi-one-dimensional systems: i) the gold wires self-assemble under the appropriate conditions thus, once these conditions have been determined, clean and well-ordered samples can be easily fabricated; ii) vicinal surfaces act as templates creating regular arrays of wires which are suitable for high resolution studies using angle-resolved photoemission; iii) furthermore, inter-chain distances and interactions can be tuned by changing the average terrace width, which can be controlled by the miscut angle; iv) due to the interaction of the gold atoms with the substrate these structures are expected to be more robust against Peierls-like distortions (remaining metallic) as compared to other quasi-one-dimensional systems like e.g. organic compounds; v) the substrate is a semiconductor so the bands appearing near the Fermi energy associated with the gold chains should reflect, at least to some extent, the properties of one-dimensional metals. Unfortunately some of these expectations have not been fully confirmed by the experiment. For example, the Si(557)-Au has been reported to suffer a Peierls-like transition to a semiconducting ground state [11], and the semiconducting or metallic character of the Si(111)-(5 \times 2)-Au surface is still a matter of debate [17,21,23].

In this context, the band structure of the Si(553)-Au surface was considered a very interesting opportunity [4,25]. This surface presents three dispersive surface bands with clear one-dimensional character. Two of them are almost identical to the nearly half-filled bands found for the Si(557)-Au surface [7]. Therefore, in analogy with this surface, these bands can be assumed to appear as a consequence of the spin-orbit splitting of a dispersive surface band associated with the gold wires [12]. The third band is metallic at room temperature and nearly 1/4 filled [25], its origin being unclear. This quarter-filled band could create a unique opportunity for observing the Luttinger liquid behavior. This is in contrast with half-filled bands, which are unstable against a Mott transition for large values of the electron-electron interaction, preventing the possible observation of a Luttinger metal [4]. Furthermore, having several surface bands with different fractional fillings could prevent the appearance of a Peierls instability if all of these bands come from the same wire in the

surface. Again some of these expectations seem to have been frustrated by the experimental evidence. A very recent study indicates that both groups of bands (the half-filled ones and the nearly $1/4$ -filled bands) come from different regions of the surface unit cell and suffer independent Peierls-like instabilities with different transition temperatures [26].

The origin of the quarter-filled band in the Si(553)-Au surface is an interesting line of research. If this band were understood, then it might be possible to envision ways to modify the surface or to fabricate analogous structures on different substrates such that one could finally observe the Luttinger metal behavior. One important step in such research program is to find a reliable structural model. This is a necessary prerequisite to understand the electronic structure of any complex surface reconstruction. To date the atomic structure of the Si(553)-Au reconstruction has not been completely established. Until quite recently all the available structural information was based on scanning tunneling microscopy (STM) studies [25-27] that, however, were not very conclusive. The reported gold coverage was 0.24 ML [25], which pointed to the existence of a monatomic gold wire in each terrace on the surface. According to this information, and to a plausible analogy with other systems like the Si(557)-Au surface, a series of structural models were investigated by Riihkonen and Sanchez-Portal [28] and Crain et al. [4]. However, none of these models provided a fully satisfactory description of the observed band structure and STM images [28]. More recently, Ghose et al. [29] have proposed a detailed structural model of the Si(553)-Au surface reconstruction based on an x-ray diffraction study. Surprisingly, their model contains twice as much gold (0.54 ML) as the original proposals. According to these authors, the gold coverage is firmly established by their analysis of the x-ray data [29]. However, it seems quite unlikely that the gold dose were so severely underestimated in the previous studies [25]. Therefore, this might imply that there exist two stable structures, with different gold content, for the Si(553)-Au surface.

In this work, we study the geometry and the electronic properties of the model proposed by Ghose et al. [29] using *ab initio* density functional calculations. We perform constrained and unconstrained relaxations, starting from the structural coordinates of Ghose and collaborators [30]. We analyze the stability, electronic band structure and simulated STM images of the model. In the light of our calculations, this geometry is not stable and the predicted band structure is quite different from that reported in the photoemission experiments.

2 Computational method

All the calculations were performed using the SIESTA code [31,33]. We used the local density approximation [34] and norm conserving pseudopotentials [35]. The gold pseudopotential included scalar relativistic effects and was similar to that used in Ref. [36] and in our previous calculations [24,28]. A double- (DZ) basis set of atomic orbitals (i.e. including two different radial functions for the 3s orbitals, and another two to represent the 3p shell) was used for silicon. The gold basis included doubled and polarized 6s orbitals (thus including a single 6p shell) and a single 5d shell. Although a DZ basis is usually sufficient to obtain a quite good description of the occupied electronic states and the relaxed geometries in silicon systems, the use of a more complete basis set is necessary to describe the unoccupied part of the band structure even at low energies. For this reason we use a double-polarized (DZP) silicon basis set for the calculation of the band structure and the STM images. We used an energy shift of 200 meV to define the cut-off radii of the different orbitals [32]. The corresponding radii are 5.25 and 6.43 Bohr for the 3s and 3p (3d) Si orbitals, and 6.24 and 4.51 Bohr for the 6s (6p) and 5d Au orbitals, respectively.

We modelled the surface using a slab formed by three silicon bilayers. The bottom silicon layer is saturated with hydrogen. To avoid artificial stresses the lateral lattice parameter was fixed to the bulk theoretical value calculated with similar approximations (5.48 Å with a DZ basis set). The structures were relaxed until the maximum force component was less than 0.04 eV/Å. The distance between neighbouring slabs was 15 Å. A 4×4 sampling of the surface Brillouin zone and a real-space grid equivalent to a 100 Ry plane-wave cut-off was used. The Tersoff-Hamann theory was used to produce the simulated STM images [37].

3 Results

The proposal for the structure of the Si(553)-Au reconstruction by Ghose et al. [29] can be seen in Fig.1 (a) and (b). The main features are the double row of gold atoms located at the step edge of the Si(553) surface and the silicon adatoms residing right below some of these gold atoms. This reconstruction is quite different from the other and better known structures induced by the deposition of gold on vicinal Si(111) surfaces like, for example, the Si(557)-Au reconstruction [10,4]. Particularly surprising is the position of the gold atoms at the step edge. It has been shown by density functional calculations in several similar surfaces that the silicon substitutional sites in the middle of the terraces are typically more favorable for gold [8,10,28]. Another striking fact is the very

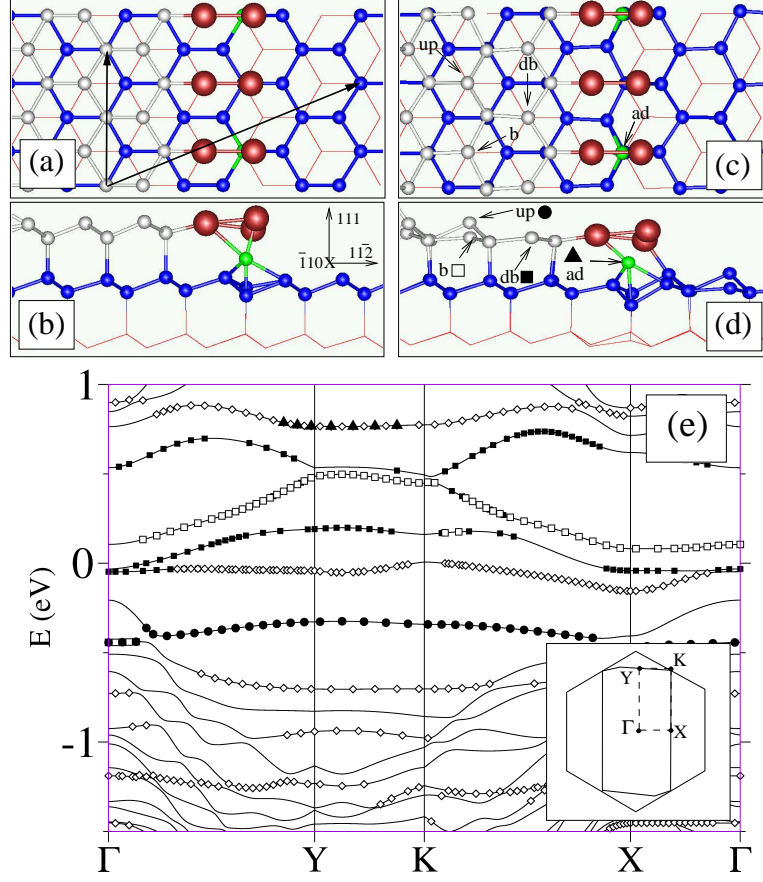


Fig. 1. The model of Ghose et. al. [29] for the Si(553)-Au reconstruction (a and b, panel (a) also shows the unit cell vectors). The same structure after constrained relaxation (c and d) and the corresponding band structure (see text). The main atomic character of the surface bands is indicated with different symbols in panel (e) which correspond to those used to label different atoms in panels (c) and (d). The diamonds correspond to the gold atoms in the step edge and their neighboring silicon atoms. The inset of panel (e) illustrates the Brillouin-zone of the Si(553)-Au reconstruction. The Brillouin-zone of a 2×2 supercell of the unreconstructed Si(111) surface is also shown for comparison. The $-Y$ and $K-X$ directions are parallel to the gold wires.

large distance between the gold atoms along the step edge (see Fig. 1 (a)). This distance (~ 3.8 Å) has to be compared, for example, to the nearest neighbor distance in bulk gold (2.9 Å). In the direction perpendicular to the step edge we find two slightly different Au-Au distances, 2.7 Å and 2.8 Å. These distances are intermediate between the bond length of the gold dimer (2.5 Å) and that of bulk. Another peculiarity of this structure is that the silicon terrace remains basically unreconstructed. This is in clear contrast with other systems like the Si(557)-Au surface [10], the Si(111)-(5 \times 2)-Au [19,20,24], and even previous theoretical models of the Si(553)-Au [28]. For example, the so-called honeycomb chain reconstruction of silicon [38] is known to occur in most of the gold induced reconstructions on vicinal Si(111) [4]. However, it is

absent in the model studied here. Thus, the gold double-row model proposed by Ghose et. al. can be pictured as a collection of gold dimers attached to the edges of the terraces of a largely unreconstructed Si(553) surface. The gold dimers are oriented along the normal to the step edge. There are two types of gold dimers. This configuration can be justified for one of these dimers, which bonds to a silicon adatom in the terrace below with a reasonable Si-Au distance of 2.4 Å. However, this arrangement seems rather artificial and unstable for the other dimer. We performed structural relaxations to study the stability of this structural model. As we will see below the model turns out to be unstable and its structure is greatly modified during the relaxation. One could always argue that this result is a pathology of the local density approximation or other approximations used in this work. For this reason we have performed constrained relaxations that, while optimizing some of the bond lengths and bond angles, preserve the main characteristics of the structure in Ref. [29]. The electronic band structure and the simulated STM images are then calculated for this optimized structure and compared to the available experimental information.

Fig. 1 (c) and (d) shows the result of a constrained relaxation in which the relative positions of the gold atoms are not allowed to change (i.e. the gold atoms cannot move respect to each other). All other degrees of freedom are optimized: i) the position of the center of mass of the gold atoms and, ii) the positions of all the silicon atoms in the slab, except those in the lowest layer which remain in perfect bulk positions. As a stronger scatterer, the gold positions should be the most reliable in the experiment [9,29]. This justifies the approach followed here. After this constrained relaxation, the silicon atoms of the first layer reconstruct to some extent. The atoms labeled "up" and "b" (see Fig. 1 (c) and (d)) give rise to a buckling of the surface, a well known silicon reconstruction [39] in which there is a charge transfer from the lower atom to the elevated one. This is clearly reflected in the electronic band structure shown in Fig. 1 (e). The "up" atom creates a fully occupied band with small dispersion (solid circles), while a more dispersive unoccupied band (open squares) is associated with the "b" atom. Atom labeled "db" has a partially occupied dangling-bond. The corresponding dispersive metallic band (solid squares) can be found close to the Fermi level in Fig. 1 (e). Several surface bands appear associated with the gold atoms and their neighboring silicon atoms in the step edge (open diamonds). However, all these bands are quite flat. This is in contrast with the band structures of other reconstructions of gold in vicinal Si(111). In those cases the gold atoms occupy silicon substitutional positions in the middle of the terraces and produce quite dispersive one-dimensional bands that dominate the photoemission spectra [10,12,20,24,28]. Furthermore, in Ref. [12] it was shown that the presence of gold induces a spin-orbit splitting of the hybrid silicon-gold bands that explains the observation of two proximal one-dimensional bands in the Si(557)-Au surface [7,11]. The photoemission of the Si(553)-Au surface also shows two proximal half-filled

bands similar to those of the Si(557)-Au [4,25,26]. Therefore, it is tempting to associate these bands with the gold wires and their silicon neighbors in analogy to the case of Si(557)-Au. Since in the present calculations we are not including the spin-orbit interaction, these two proximal bands should appear as a single dispersive band [12]. Unfortunately, a dispersive band associated with the gold atoms is completely absent in Fig. 1 (e). The band coming from the partially occupied dangling-bonds in the "db" atoms could be identified with the $1/4$ filled band of the Si(553)-Au [4,25,26]. However, this identification is also not very clear since in the experiment this band goes down to much lower energies. We can thus conclude that the band structure calculated for the model proposed by Ghose et al. fails to reproduce the photoemission data. Of course, given the discrepancy in the gold coverage reported in the photoemission work [4,25] and the x-ray diffraction work of Ghose et al. [29], it is perfectly plausible that we are dealing with different reconstructions of the surface. In such case, the data reported in Fig. 1 (e) can be considered as the predicted electronic band structure for the double row model proposed by Ghose et al. using the local density approximation.

Simulated STM images for filled and empty states are presented in Fig. 2. The gold atoms show as alternating bright spots along the $[110]$ direction with a $\sqrt{2}$ periodicity. This periodicity reflects the alternating heights of the gold atoms induced by the presence of a row of silicon adatoms below them. Another feature with $\sqrt{2}$ periodicity is seen in the middle of the terrace as a result of the buckling of the silicon surface layer. In spite of the difference in the reported gold coverages we can insist in comparing with the available experimental images [4,25{27}]. At room temperature the step edge is observed in the experiment as a continuous bright line. Another less pronounced feature is found in the middle of the terrace with a $\sqrt{2}$ modulation already at room temperature. At low temperature the terrace chain shows a more clear $\sqrt{2}$ periodicity, while the line at the step edge develops a $\sqrt{3}$ modulation. While the doubling of the periodicity in the middle of the terrace is reproduced by the model studied here, the image produced by the step edge is quite different. The appearance of bright spots in the step edge is linked to the presence of the silicon adatom in the terrace below. One could then speculate on creating a better agreement with the STM images by introducing an adatom only every three unit cells. However, this could hardly produce the observed temperature variation. We can thus conclude that the STM images predicted for the double row model of the Si(553)-Au reconstruction differ considerably from the reported STM images.

So far we have analyzed the results obtained for a structure optimized under the restriction that the gold atoms remain at the experimentally determined positions. We can now release this constraint and, starting from this partially relaxed structure, fully optimize the geometry of the surface. By doing this we discover that the proposal of Ghose et al. is not stable, at least within

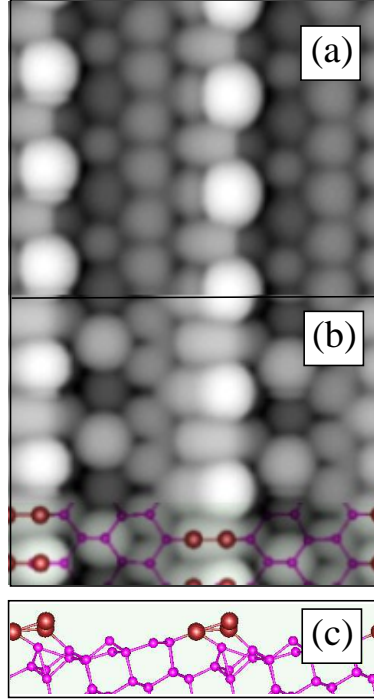


Fig. 2. Simulated STM images of the double row model [29] of the Si(553)-Au reconstruction after constrained relaxation: panel (a) for a +1.0 V bias voltage (empty states), and (b) for -1.0 V bias voltage (filled states). Panel (c) shows the corresponding atomic configuration viewed from the side.

our computational approach. Although we do not find strong changes in the silicon terrace, the structure of the gold double-row is completely modified. This is clearly seen in Fig. 3, where we show the structure of the surface after 300 steps of unconstrained structural relaxation. The gold atom that was initially sited on top of the silicon adatom has moved to a new position on top of the neighboring rest-atom. The configuration of the silicon adatom has also changed considerably. The adatom moves to a higher position, its height over the terrace being now comparable to that of the gold atoms. This movement is possible because the adatom breaks a bond with one of the silicon surface atoms and adopts a bridge-like configuration. This broken bond is replaced by a new Si-Au bond. Although the structure shown in Fig. 3 is not completely relaxed, it becomes clear that the model of the surface proposed in Ref. [29], based on a silicon step edge decorated with gold dimers, is not stable. In particular, the adsorption of one of the gold atoms on top of a silicon adatom is avoided. This is consistent with previous density functional calculations [10,20]. In these calculations it was shown that the adsorption of gold as an adatom over the silicon surface is quite unfavorable compared to the substitution of the gold atoms in the surface layer.

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Fig. 3. Top (a) and lateral (b) view of the double row model [29] of the Si(553)-Au after 300 steps of unconstrained structural relaxation.

4 Conclusions

In this work we present *ab initio* density functional calculations of the double row model proposed by Ghose et al. [29] for the Si(553)-Au reconstruction. We address the stability of the model, as well as its electronic band structure and STM images. Using the geometry obtained in a constrained structural relaxation, which preserves the main characteristic of the proposal of Ref. [29], we calculate the band structure and STM images. We only find a dispersive band with fractional filling close to the Fermi level. This band comes from the silicon dangling-bonds in the surface and its energy position and filling seems quite different from the bands observed in the photoemission experiments [25,26]. Dispersive bands associated with the gold atoms and their silicon neighbors are completely absent, which also seems to be in disagreement with the experimental evidence [12,25,26]. At variance with the room temperature experimental STM images [25,26], our simulated STM images do not show the step edge as a continuous bright line, but exhibit a $\sqrt{2}$ modulation associated with the presence of the adatoms in the neighboring terrace. In the low temperature experimental images the step edge develops a $\sqrt{3}$ periodicity [26]. It might be possible to induce this $\sqrt{3}$ periodicity in our calculated STM images by modifying the adatom content. However, it is not clear how this could reproduce the temperature dependence. In summary, the calculated band structure and STM images for the model proposed in Ref. [29] do not provide a good agreement with the available experimental information for this surface. Of course, it might be argued that this is a consequence of the different gold coverage in the different experimental approaches [25,29]. In fact, it is possible that the surface reconstructions studied by x-ray diffraction in Ref. [29] and by photoemission and STM in references [25], [26], and [27] are different. Unfortunately, the structure provided by Ghose et al. [29] is unstable, at least at the level of the local density approximation. When the geometry is relaxed without any constraints the structure of the gold double-row attached to the step edge severely modifies from the proposal of Ref. [29]. Therefore, we propose that the data of Ghose et al. should be reanalyzed in the light of the present results and new proposal for the structure of the Si(553)-Au surface obtained.

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